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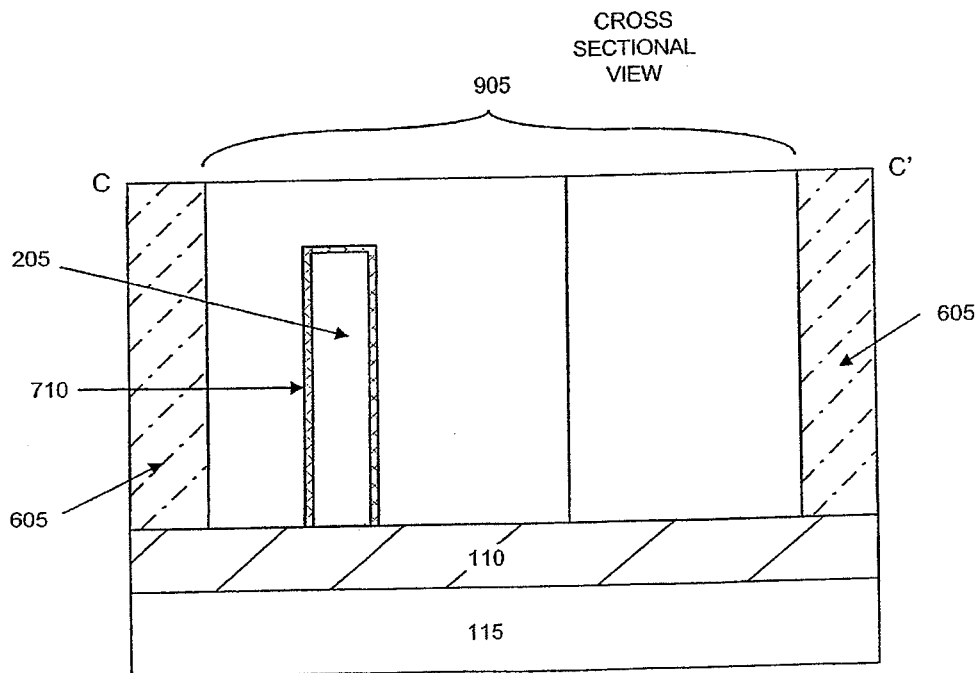
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(54) Title: **DAMASCENE TRI-GATE FINFET**



(57) Abstract: A method of forming a fin field effect transistor includes forming a fin (205) and forming a source region (210) adjacent a first end of the fin (205) and a drain region (210) adjacent a second end of the fin (205). The method further includes forming a dummy gate (505) over the fin (205) and forming a dielectric layer (605) around the dummy gate (505). The method also includes removing the dummy gate (505) to form a trench (705) in the dielectric layer (605) and forming a metal gate (905) in the trench (705).